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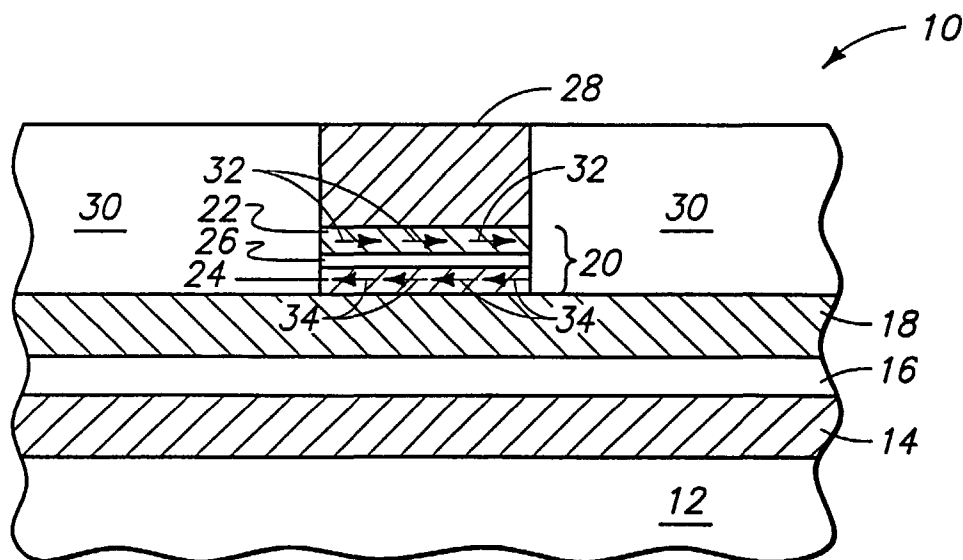
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(54) Title: **MAGNETORESISTIVE MEMORY DEVICES AND ASSEMBLIES; AND METHODS OF STORING AND RETRIEVING INFORMATION**



(57) **Abstract:** The invention encompasses a magnetoresistive memory device. The device includes a memory bit which comprises a stack having a first magnetic layer, a second magnetic layer, and a non-magnetic layer between the first and second magnetic layers. A first conductive line is proximate the stack and configured for utilization in reading information from the memory bit. A second conductive line is spaced from the stack by a greater distance than the first conductive line is spaced from the stack, and is configured for utilization in writing information to the memory bit. The invention also encompasses methods of storing and retrieving information in a cross-point array architecture.



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